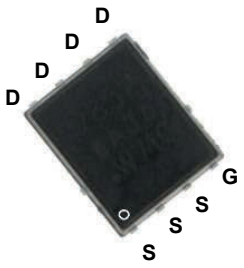
GOOD-ARK SEMICONDUCTOR

GSFP68015

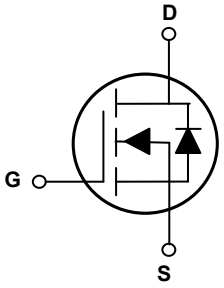
150V N-Channel MOSFET

Main Product Characteristics

$V_{(BR)DSS}$	150V
$R_{DS(ON)}$	52mΩ (Typ)
I_D	20A



PPAK5x6



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

Description

The GSFP68015 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-to-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, @ Steady-State (T_C=25°C)[1]	I_D	20	A
Continuous Drain Current, @ Steady-State (T_C=100°C)		14	A
Pulsed Drain Current[2]	I_{DM}	80	A
Power Dissipation (T_C=25°C)	P_D	75	W
Linear Derating Factor (T_C=25°C)		0.6	W/°C
Single Pulse Avalanche Energy[3]	E_{AS}	25	mJ
Junction-to-Case	$R_{\theta JC}$	1.6	°C/W
Junction-to-Ambient (PCB Mounted, Steady-State)[4]	$R_{\theta JA}$	50	°C/W
Operating Junction and Storage Temperature Range	T_J/T_{STG}	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	150	-	-	V
Drain-to-Source Leakage Current	I_{DSS}	V_{DS}=150V, V_{GS}=0V	-	-	1	μA
		T_J=125°C	-	-	50	
Gate-to-Source Forward Leakage	I_{GSS}	V_{GS}=20V	-	-	100	nA
		V_{GS}=-20V	-	-	-100	
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=5A	-	52	68	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	2.1	3	3.9	V
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=75V, f=1MHz	-	518	-	pF
Output Capacitance	C_{oss}		-	76	-	
Reverse Transfer Capacitance	C_{rss}		-	3.3	-	
Total Gate Charge	Q_g	I_D=5A, V_{DS}=75V, V_{GS}=10V	-	9.1	-	nC
Gate-to-Source Charge	Q_{gs}		-	3.5	-	
Gate-to-Drain ("Miller") Charge	Q_{gd}		-	1.8	-	
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V, V_{DS}=30V, I_D=5A, R_{GEN}=6Ω	-	7.3	-	nS
Rise Time	t_r		-	24	-	
Turn-Off Delay Time	$t_{d(off)}$		-	14	-	
Fall Time	t_f		-	22	-	
Gate Resistance	R_g	f=1MHz	-	2.5	-	Ω
Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	20	A
Pulsed Source Current (Body Diode)	I_{SM}		-	-	80	A
Diode Forward Voltage	V_{SD}	I_S=2A, V_{GS}=0V	1	-	1.2	V
Reverse Recovery Time	T_{rr}	I_S=5A, V_{GS}=0V di/dt=100A/us	-	53	-	uS
Reverse Recovery Charge	Q_{rr}		-	0.11	-	nC

Notes

1. Pulse test: pulse width≤300us, duty cycle ≤2%.
2. Repetitive rating; pulse width limited by max. junction temperature.
3. L=0.5mH, R_G=25Ω, V_{DD}=50V, I_{AS}=10A, T_J=25°C.
4. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

Typical Electrical and Thermal Characteristic Curves

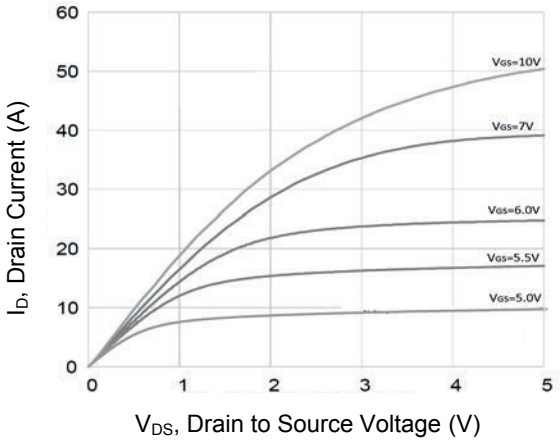


Figure 1. Typical Output Characteristics

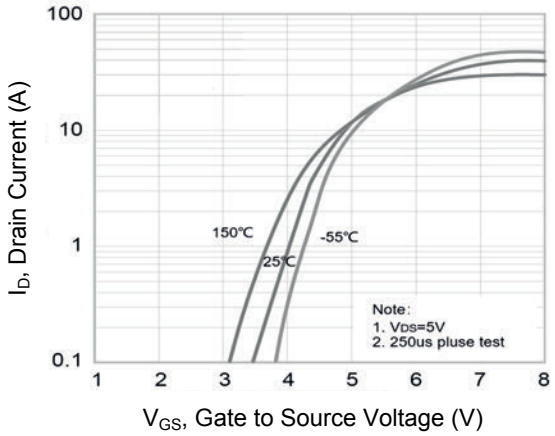


Figure 2. Transfer Characteristics

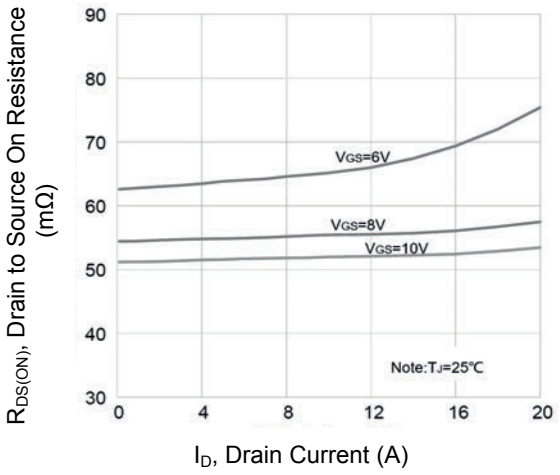


Figure 3. $R_{DS(ON)}$ Vs. Drain Current

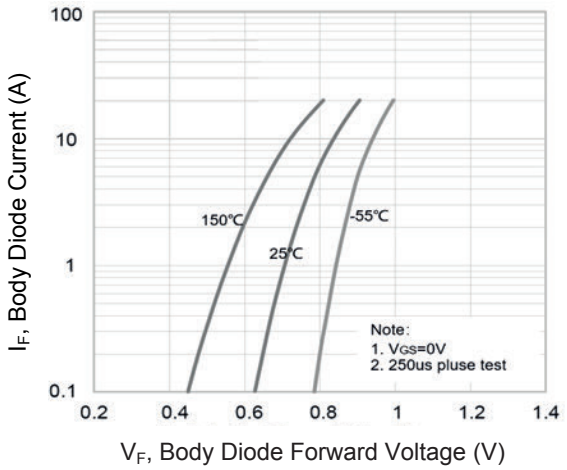


Figure 4. Body Diode Characteristics

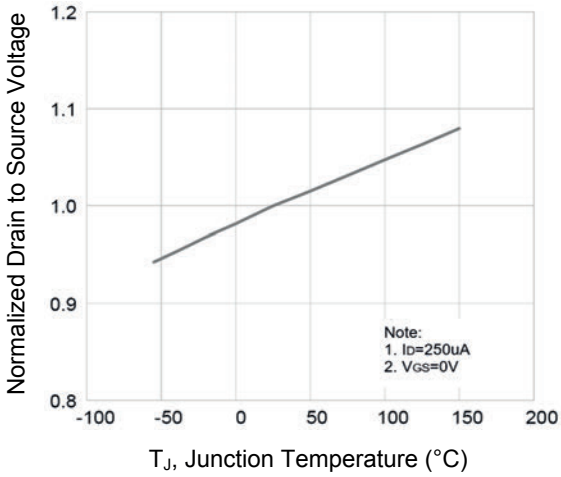


Figure 5. Normalized BV_{DSS} Vs. T_J

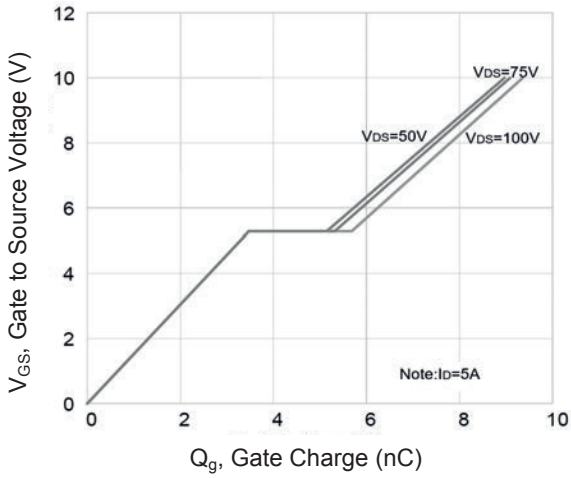


Figure 6. Gate Charge

Typical Electrical and Thermal Characteristic Curves

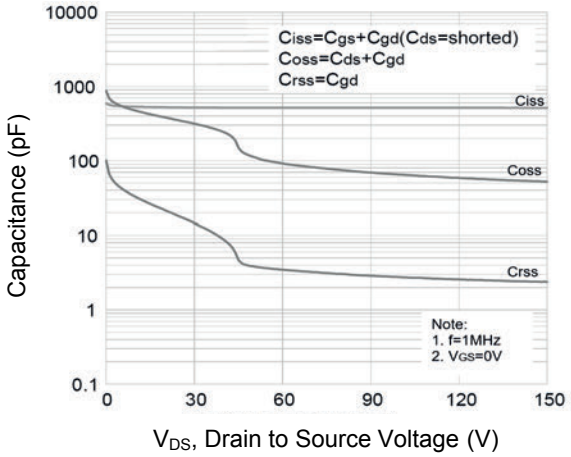


Figure 7. Capacitance Characteristics

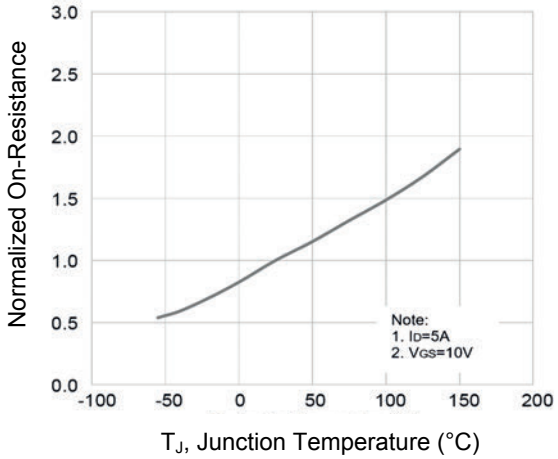
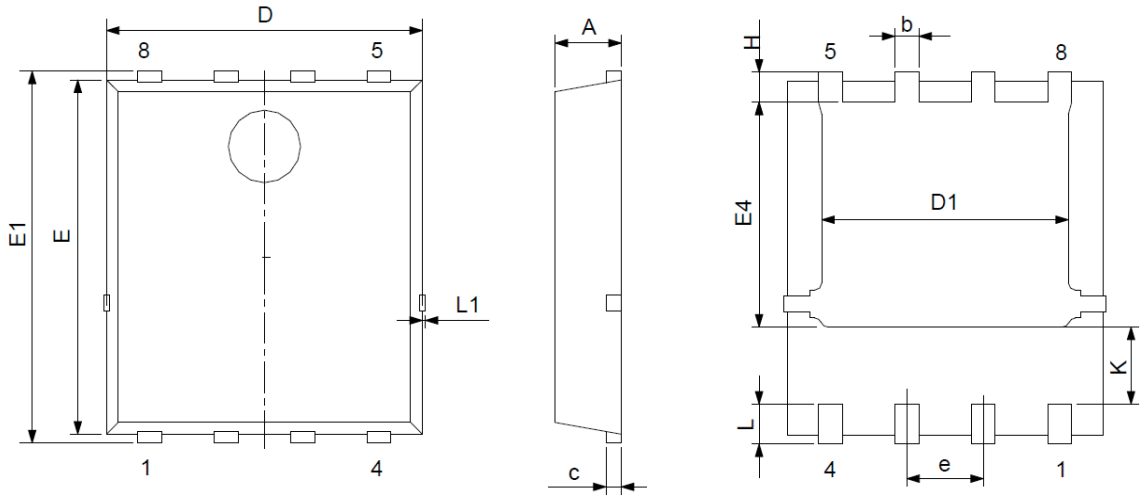


Figure 8. Normalized $R_{DS(ON)}$ Vs. T_J

Package Outline Dimensions (PPAK5x6)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.200	0.035	0.047
c	0.154	0.354	0.006	0.014
D	4.800	5.400	0.189	0.213
E	5.660	6.060	0.223	0.239
D1	3.760	4.300	0.148	0.169
E1	5.900	6.350	0.232	0.250
b	0.300	0.550	0.012	0.022
k	1.100	1.500	0.043	0.059
e	1.070	1.370	0.042	0.054
E4	3.340	3.920	0.131	0.154
L	0.300	0.710	0.012	0.028
L1	-	0.120	-	0.005
H	0.400	0.710	0.016	0.028